

**TO-252
(DPAK)**

Pin Definition:

1. Base
2. Collector
3. Emitter

PRODUCT SUMMARY

BV_{CBO}	50V
BV_{CEO}	50V
I_C	3A
V_{CE(SAT)}	0.5V @ I _C / I _B = 2A / 200mA

Features

- Low V_{CE(SAT)} 0.25 @ I_C / I_B = 2A / 200mA (Typ.)
- Complementary part with TSB1184CP

Structure

- Epitaxial Planar Type
- NPN Silicon Transistor

Ordering Information

Part No.	Package	Packing
TSD1760CP RO	TO-252	2.5Kpcs / 13" Reel

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	DC	3	A
	Pulse	7 (note 1)	
Power Dissipation	Ta=25°C	1 (note 2)	W
	Tc=25°C	15	
Operating Junction Temperature	T _J	+150	°C
Operating Junction and Storage Temperature Range	T _{STG}	- 55 to +150	°C

Note: 1. Single pulse, Pw=10mS, Duty≤2%

2. PCB 1.7mm thick, collector copper plating 10mm x 10mm or larger.

Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	I _C = 50uA, I _E = 0	BV _{CBO}	50	--	--	V
Collector-Emitter Breakdown Voltage	I _C = 1mA, I _B = 0	BV _{CEO}	50	--	--	V
Emitter-Base Breakdown Voltage	I _E = 50uA, I _C = 0	BV _{EBO}	5	--	--	V
Collector Cutoff Current	V _{CB} = 30V, I _E = 0	I _{CBO}	--	--	1	uA
Emitter Cutoff Current	V _{EB} = 4V, I _C = 0	I _{EBO}	--	--	1	uA
Collector-Emitter Saturation Voltage	I _C / I _B = 2A / 200mA	*V _{CE(SAT)}	--	0.25	0.5	V
DC Current Transfer Ratio	V _{CE} = 2V, I _C = 100mA	*h _{FE}	82	--	560	
Transition Frequency	V _{CE} = 5V, I _C = 50mA, f = 100MHz	f _T	--	90	--	MHz
Output Capacitance	V _{CB} = 10V, f = 1MHz	Cob	--	45	--	pF

* Pulse Test: Pulse Width ≤380uS, Duty Cycle≤2%

Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

Figure 1. DC Current Gain

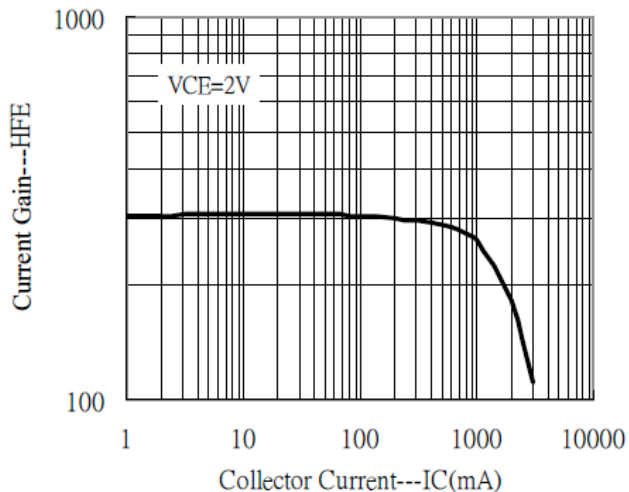


Figure 2. VCE(SAT) V.s. IC

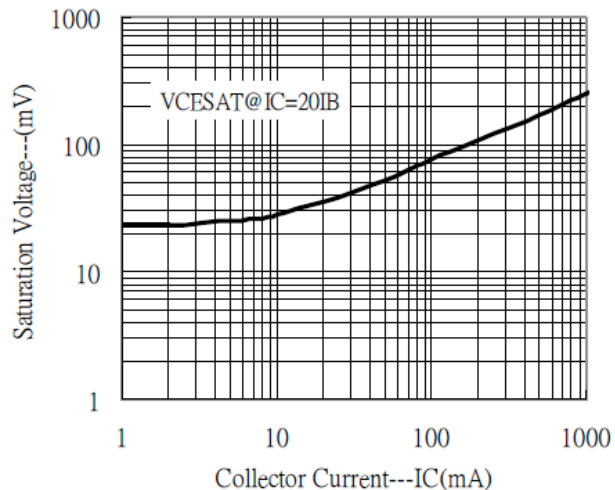


Figure 3. VBE(SAT) V.s. IC

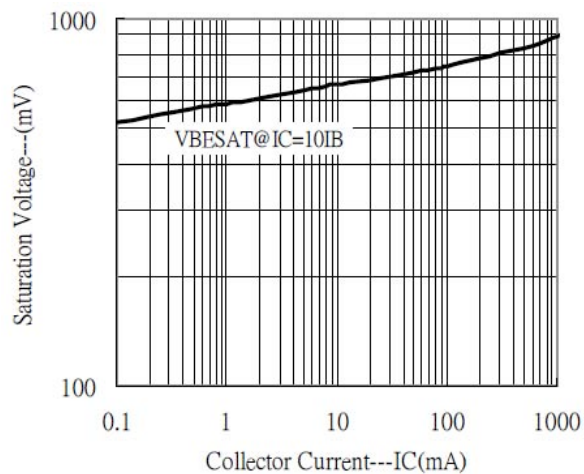
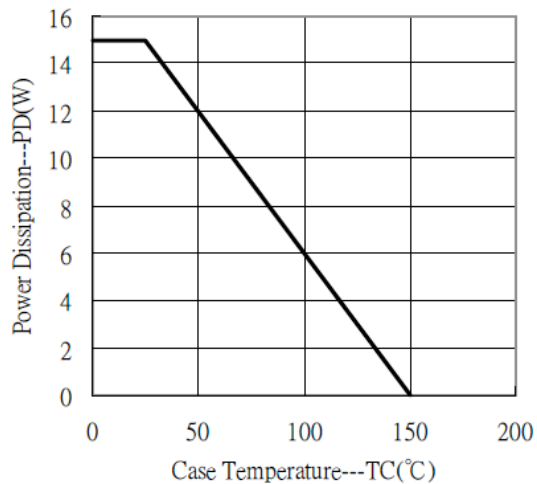
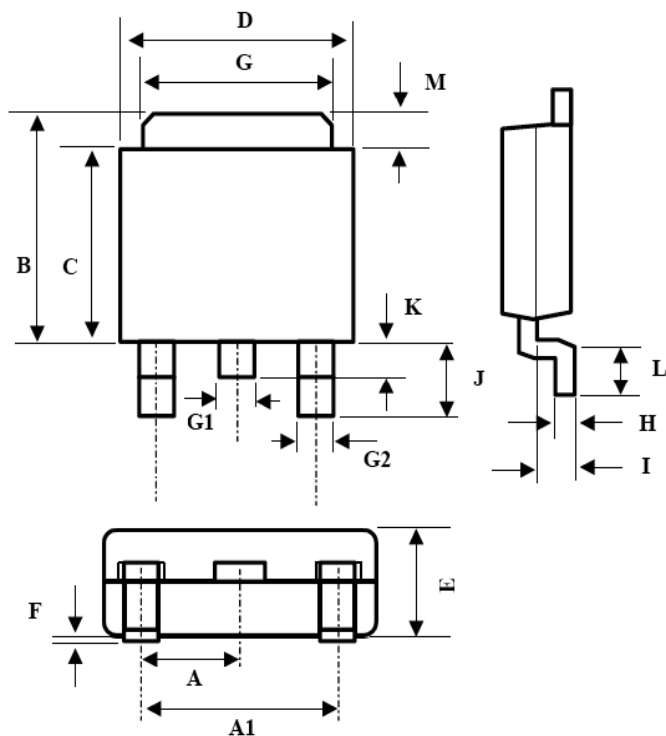


Figure 4. Power Derating Curve



TO-252 Mechanical Drawing



TO-252 DIMENSION				
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.3BSC		0.09BSC	
A1	4.6BSC		0.18BSC	
B	6.80	7.20	0.268	0.283
C	5.40	5.60	0.213	0.220
D	6.40	6.65	0.252	0.262
E	2.20	2.40	0.087	0.094
F	0.00	0.20	0.000	0.008
G	5.20	5.40	0.205	0.213
G1	0.75	0.85	0.030	0.033
G2	0.55	0.65	0.022	0.026
H	0.35	0.65	0.014	0.026
I	0.90	1.50	0.035	0.059
J	2.20	2.80	0.087	0.110
K	0.50	1.10	0.020	0.043
L	0.90	1.50	0.035	0.059
M	1.30	1.70	0.051	0.67

TSD1760

Low Vcesat NPN Transistor

Notice

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[Taiwan Semiconductor:](#)

[TSD1760CP](#)